As described herein before, according to the preferred embodiment invention, the liquid crystal display device can have a high aperture ratio, a high display quality and a high contrast ratio. Further, the liquid crystal display device can be manufactured by a simplified process. Besides, the dazzling of the screen due to the reflection of incident light can be prevented.

In the Claims:

Please amend the claims as follows:

1. (Amended) A liquid crystal display device, comprising:

a display panel;

a first substrate forming an uppermost layer of said display panel, including:

a) a switching element on the first substrate

b) a passivation film formed over the whole surface of the first substrate while covering the switching element;

c) a pixel electrode on the passivation film;

d) a black matrix formed on the passivation film and over the switching element;

e) a color filter formed over the pixel electrode; and

f) a first orientation film formed on the black matrix and the color filter and above the pixel electrode;

a second substrate aligned with the first substrate and formed adjacent to a backlight device, to prevent the degradation of contrast resulting from the mixing of dispersed light, having a common electrode and a second orientation film, the orientation film formed on the common electrode;

sealing the first and second substrates with a sealant; and

a liquid crystal layer interposed between the first and second substrates.

2. (Amended) The liquid crystal display device of claim 1, wherein the switching element is a thin film transistor, the thin film transistor having a gate electrode formed on the first substrate, a gate insulating layer formed on the exposed surface of the first substrate while covering the gate electrode, a semiconductor layer formed over the gate electrode, a source electrode overlapping one end portion of the semiconductor layer, and a drain electrode overlapping the other end portion of the semiconductor layer.

7. (Amended) The liquid crystal display device of claim 5, wherein the back light device is for supplying light to the liquid crystal layer.

12. (Amended) A method of manufacturing a liquid crystal display device which comprises an array of thin film transistors and an array of pixel electrodes including:

forming a gate line and a gate electrode on a first substrate said first substrate forming the uppermost layer of a display panel, the gate electrode extending from the gate line;

forming a gate insulating layer on the exposed surface of the upper substrate while covering the gate line and the gate electrode;

forming a semiconductor layer over the gate electrode;

forming a data line and source and drain electrodes, the source electrode overlapping one end portion of the semiconductor layer, the drain electrode overlapping the other end portion of the semiconductor layer, the source and drain electrodes spaced apart from each other, the source electrode extending from the data line;

forming a passivation film over the whole surface of the first substrate while covering the source and drain electrodes, the passivation film having a contact hole on the drain electrode;

forming a pixel electrode on the passivation film, the pixel electrode electrically connected with the drain electrode through the contact hole;

forming a color filter on the pixel electrode;

forming a black matrix over the thin film transistor;

forming a first orientation film on the color filters and the black matrices;

forming a common electrode on a second substrate;

forming a second orientation film on the common electrode;

aligning the first substrate turned upside down with the second substrate so that the first orientation film of the first substrate is opposite to the second orientation film of the second substrate with a gap there between to prevent degradation of the contact resulting from the mixing of dispersed light;

sealing the first and second substrates with a sealant; and

injecting a liquid crystal between the first substrate and the second substrate.

13. (Amended) The method of claim 12, further comprising:

forming a first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the source and drain electrodes.

14. (Amended) The method of claim 12, further comprising:

forming a first light absorbing film between the first substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the gate insulating layer.